

Standard Rectifier Module

$$V_{RRM} = 2 \times 1600 \text{ V}$$

$$I_{FAV} = 50 \text{ A}$$

$$V_F = 1.09 \text{ V}$$

Phase leg

Part number

MDMA50P1600TG



Backside: isolated

 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1700	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1600	V
I_R	reverse current	$V_R = 1600\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			50	μA
		$V_R = 1600\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			1.5	mA
V_F	forward voltage drop	$I_F = 50\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.13	V
		$I_F = 100\text{ A}$				1.34	V
		$I_F = 50\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1.09	V
		$I_F = 100\text{ A}$				1.37	V
I_{FAV}	average forward current	$T_C = 100^{\circ}\text{C}$ rectangular	$T_{VJ} = 150^{\circ}\text{C}$ d = 0.5			50	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^{\circ}\text{C}$		0.80	V
r_F	slope resistance					5.7	m Ω
R_{thJC}	thermal resistance junction to case					0.65	K/W
R_{thCH}	thermal resistance case to heatsink				0.2		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				190	W
I_{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}\text{C}$			850	A
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			920	A
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150^{\circ}\text{C}$			725	A
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			780	A
I^2t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}\text{C}$			3.62	kA ² s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			3.52	kA ² s
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150^{\circ}\text{C}$			2.63	kA ² s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			2.53	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$			27		pF

Package TO-240AA				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal				200	A
T_{VJ}	virtual junction temperature			-40		150	°C
T_{op}	operation temperature			-40		125	°C
T_{stg}	storage temperature			-40		125	°C
Weight					76		g
M_D	mounting torque			2.5		4	Nm
M_T	terminal torque			2.5		4	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	13.0	9.7			mm
$d_{Spb/Apb}$		terminal to backside	16.0	16.0			mm
V_{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	4800			V
		t = 1 minute		4000			V



Part description

M = Module
 D = Diode
 M = Standard Rectifier
 A = (up to 1800V)
 50 = Current Rating [A]
 P = Phase leg
 1600 = Reverse Voltage [V]
 TG = TO-240AA

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDMA50P1600TG	MDMA50P1600TG	Box	36	513022

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}\text{C}$



Rectifier

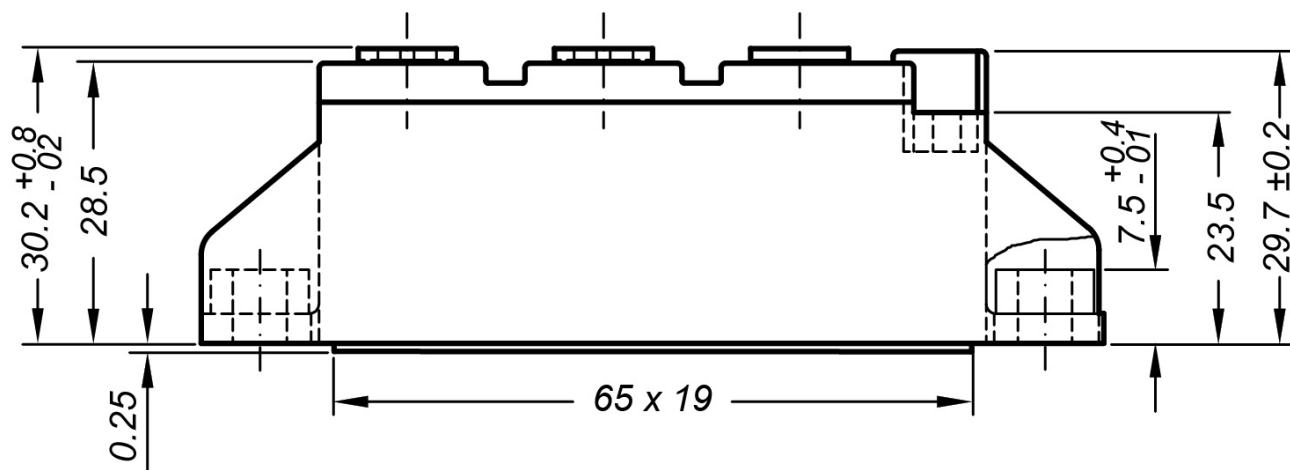
$V_{0\max}$ threshold voltage 0.8

V

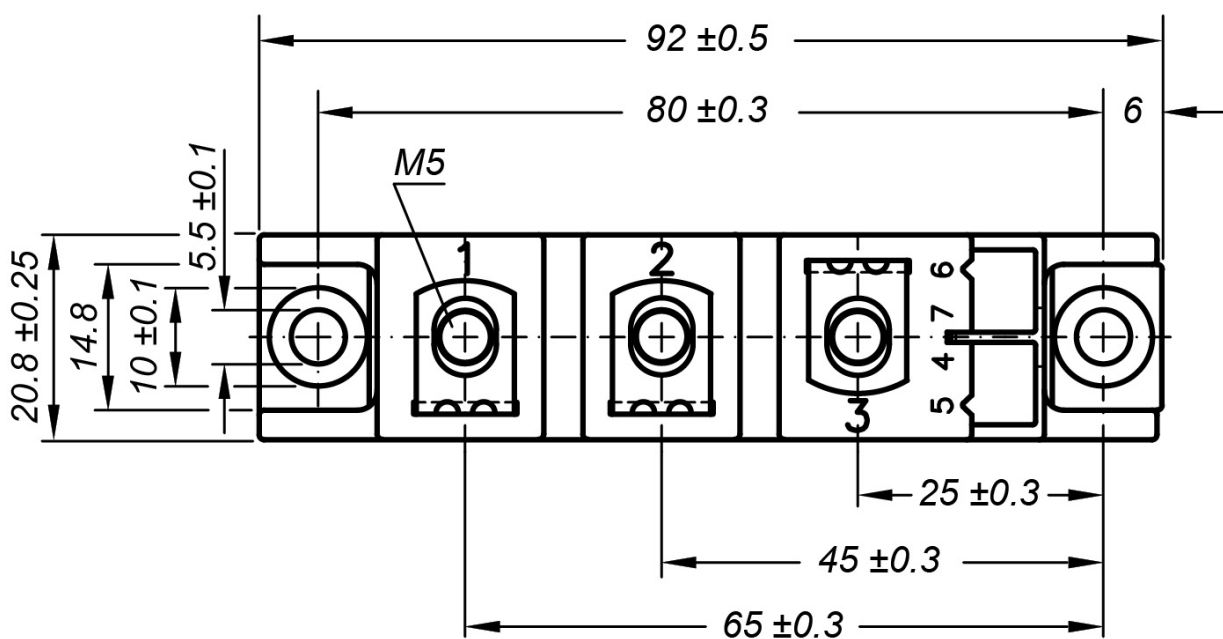
$R_{0\max}$ slope resistance * 4.5

mΩ

Outlines TO-240AA



General tolerance: DIN ISO 2768 class „c“



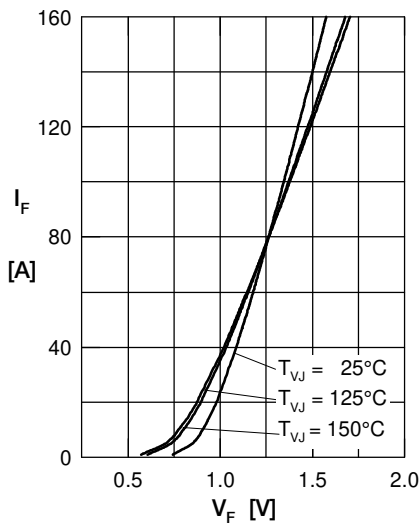
Rectifier


Fig. 1 Forward current versus voltage drop per diode

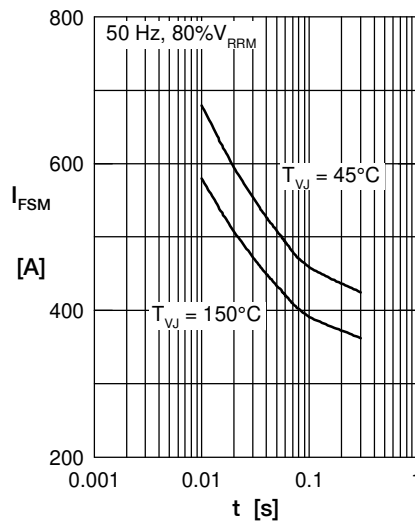


Fig. 2 Surge overload current vs. time per diode

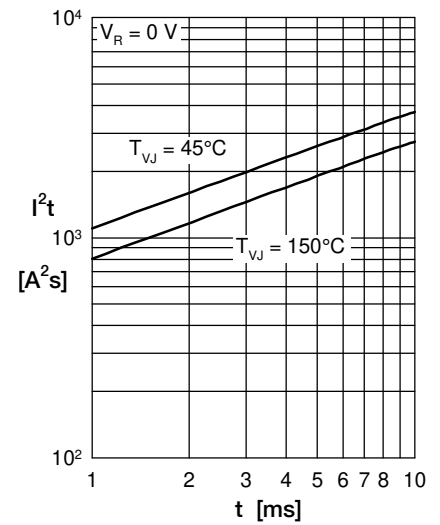
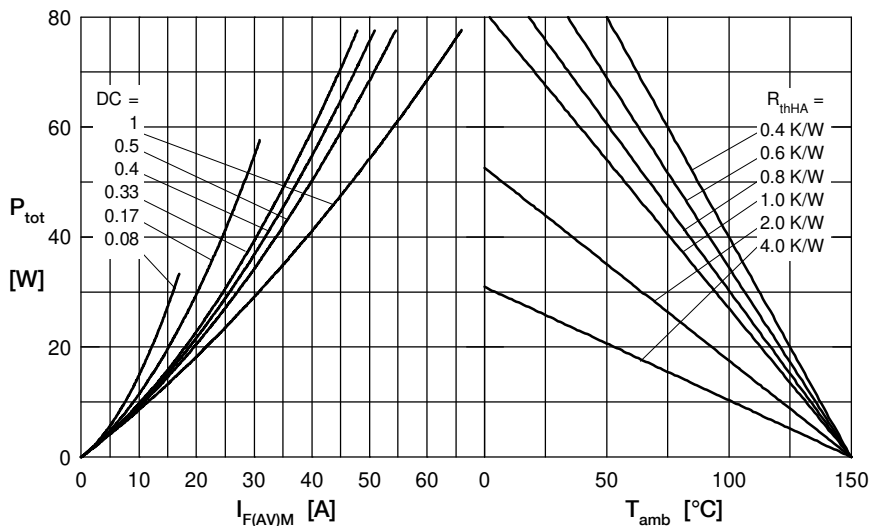

 Fig. 3 I^2t versus time per diode


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

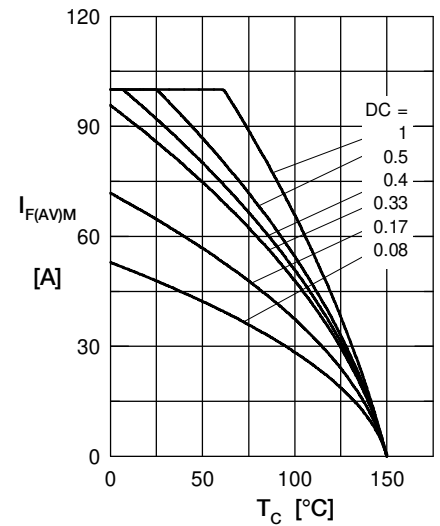


Fig. 5 Max. forward current vs. case temperature per diode

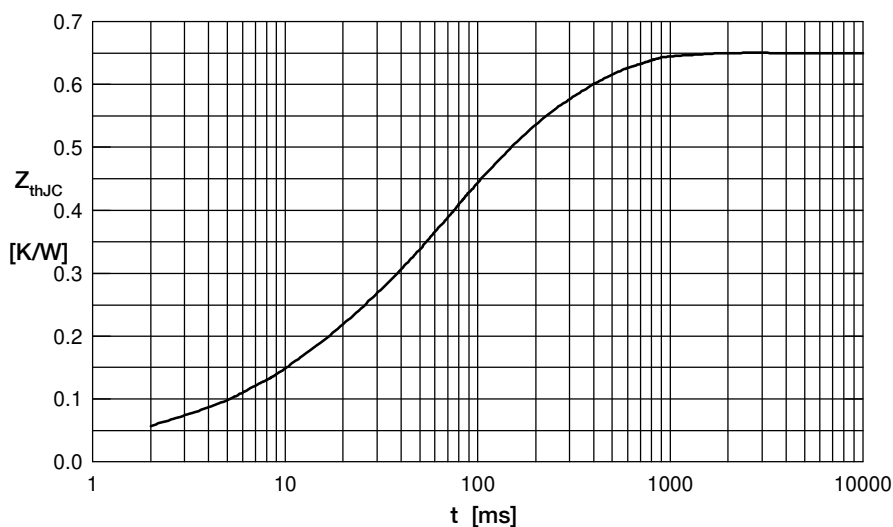


Fig. 6 Transient thermal impedance junction to case vs. time per diode

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.032	0.001
2	0.098	0.010
3	0.305	0.060
4	0.215	0.270